

Hybrid CoolSiC™ IGBT

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	650	V
DC collector current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ value limited by bondwire $T_c = 100^{\circ}\text{C}$	I_C	80.0 56.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	200.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$	-	200.0	A
Diode forward current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$	I_F	33.7 22.8	A
Diode pulsed current, t_p limited by T_{vjmax} ¹⁾	I_{Fpuls}	75.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GE}	± 20 ± 30	V
Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 100^{\circ}\text{C}$	P_{tot}	305.0 152.5	W
Operating junction temperature	T_{vj}	-40...+175	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55...+150	$^{\circ}\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R_{th} Characteristics						
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		-	-	0.50	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		-	-	1.50	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		-	-	40	K/W

¹⁾ Pulse current level depends on T_{vj} of diode chip, see also Fig. "Maximum pulse current as a function of junction temperature"

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Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0\text{V}$, $I_C = 50.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	1.65	2.10	V
Diode forward voltage	V_F	$V_{GE} = 0\text{V}$, $I_F = 20.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	1.35	1.50	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.50\text{mA}$, $V_{CE} = V_{GE}$	3.2	4.0	4.8	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650\text{V}$, $V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$	-	-	700	μA
Zero gate voltage collector current	I_{CES}	$V_{CE} = 480\text{V}$, $V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$	-	-	25	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20\text{V}$, $I_C = 50.0\text{A}$	-	62.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$ $f = 250\text{kHz}$	-	2660	-	pF
Output capacitance	C_{oes}		-	320	-	
Reverse transfer capacitance	C_{res}		-	10	-	
Gate charge	Q_G	$V_{CC} = 520\text{V}$, $I_C = 50.0\text{A}$, $V_{GE} = 15\text{V}$	-	120.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 25^{\circ}\text{C}$,	-	21	-	ns
Rise time	t_r	$V_{CC} = 400\text{V}$, $I_C = 25.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$,	-	6	-	ns
Turn-off delay time	$t_{d(off)}$	$R_{G(on)} = 12.0\Omega$, $R_{G(off)} = 12.0\Omega$,	-	180	-	ns
Fall time	t_f	$L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E	-	18	-	ns
Turn-on energy	E_{on}	Energy losses include "tail" and diode reverse recovery.	-	0.20	-	mJ
Turn-off energy	E_{off}		-	0.18	-	mJ
Total switching energy	E_{ts}		-	0.38	-	mJ